

GaAs Schottky Devices

Low R_s Flip Chip

MS8150 - P2613



Size: 26 x 13 mils Thickness: 5 mils

Bond Pad Size: 5 x 8 mils

Features

• Capacitance (65 fF Typ.)

• Low Series Resistance (3 Ω Typ.)

• Cut-off Frequency > 500 GHz

· Large Gold Bond Pads

Specifications @ 25°C (Per Junction)

• $V_F (1 \text{ mA}): 650-750 \text{ mV}$

• R_s (10 mA): 7 Ω Max.

• I_R (3 V): 10 μ A Max.

• C_T (0 V): 80 fF Max.

Maximum Ratings

Insertion Temperature	250°C for 10 Seconds				
Incident Power	+20 dBm @ 25°C				
Forward Current	15 mA @ 25°C				
Reverse Voltage	3 V				
Operating Temperature	-55°C to +125°C				
Storage Temperature	-65°C to +150°C				



Description

The MS8150-P2613 is a GaAs flip chip Schottky diode designed for use as mixer and detector elements at microwave and millimeter wave frequencies. Their high cut-off frequency insures good performance at frequencies to 100 GHz. Applications include: transceivers, digital radios and automotive radar detectors.

These flip chip devices incorporate Microsemi's expertise in GaAs material processing, silicon nitride protective coatings and high temperature metallization. They have large, 5 x 8 mil, bond pads for ease of insertion. The MS8150-P2613 is priced for high volume commercial and industrial applications.

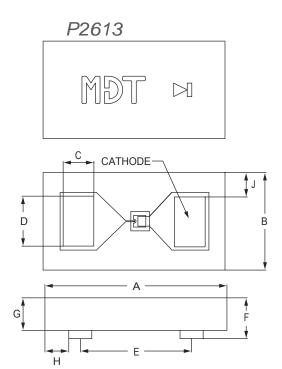
IMPORTANT: For the most current data, consult our website: <u>www.MICROSEMI.com</u> Specifications are subject to change. Consult factory for the latest information.

These devices are ESD sensitive and must be handled using ESD precautions.

¹ The MS8150 Series of products are supplied with a RoHS complaint Gold finish.



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DIM	INC	HES	MM			
DIM	MIN.	MAX.	MIN.	MAX.		
Α	0.0255	0.0265	0.6480	0.6730 0.3430 0.1420 0.2160 0.4570 0.1520 0.1400		
В	0.0125	0.0135	0.3180			
С	0.0046	0.0056	0.1170			
D	0.0075	0.0085	0.1910			
Е	0.0170	0.0180	0.4320			
F	0.0050	0.0060	0.1270			
G	0.0045	0.0055	0.1140			
Н	0.0016	0.0020	0.0406	0.0508		
J	0.0023	0.0027	0.0584	0.0686		

Spice Model Parameters (Per Junction)

	I_S	R_S	N	TT	C _{JO}	C_P	М	EG	V_{J}	BV	IBV
ſ	Α	Ω		Sec	pF	pF		eV	V	V	Α
	2 x10 ⁻¹³	3	1.2	0	0.045	0.02	0.50	1.42	0.85	4	1 x 10⁻⁵

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